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In re Application of:

JAMES R. KAHN et al.

Serial No. 09/766,069

Group Art Unit: 1745

Filed: January 19, 2001

APPARATUS FOR SPUTTER DEPOSITION

Examiner: J. A. Mercado

For: GATE SUPPORT SYSTEM

Attorney Docket No. 353-05

OFFICIAL

PROPOSED AMENDMENT

Responsive to the Examiner's Answer mailed September 23, 2003, applicant's propose the following amendment to claim 1 of the above-identified application to overcome the current rejection of claims 1-4:

Please amend claim 1 to read as follows:

1. A sputtering apparatus for use in an evacuated volume comprising:

ion source means for ionizing an ionizable gas to produce a plasma, wherein ions leaving said ion source means are in the form of an ion efflux having an energy of about 50 eV or less;

a sputter target, biased negative relative to ground, and having a curved target surface, wherein said curved target surface has a smooth continuous curvature in one direction, and wherein said curved target surface is disposed in the ion efflux of said ion source means, whereby particles of material are sputtered from said target;

a deposition substrate upon which the material sputtered from said sputter target is deposited;